

SHEET 1 OF 1

FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-066

APPLICANT(S): Westhoff et al.

SERIAL NO.: 10/765,372

FILING DATE: January 27, 2004 GROUP: ~~2812~~ 2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>ABM</i>	A1	4,914,488	04/03/1990	Yamane et al			
	A2	4,960,728	10/02/1990	Schaake et al			
	A3	6,208,005	03/27/2001	Mitra			
	A4	6,515,335	02/04/2003	Christiansen et al			
	A5	2002/0185686	12/12/2002	Christiansen et al			

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.

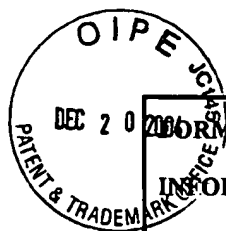
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>ABM</i>	C1	International Search Report for International Application No. PCT/US2004/002282 10/15/04

EXAMINER

ABMelson

DATE CONSIDERED

10/19/05



DEC 20 2004 OIP E J C PATENT & TRADEMARK OFFICE FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff <i>et al.</i> SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: ²⁸²³ 2812				
U.S. PATENT DOCUMENTS								
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>dm</i>	A6	2001/0003364	06/14/2001	Sugawara <i>et al.</i> ✓	7			
	A7	2001/0014570	08/16/2001	Wenski <i>et al.</i> ✓				
	A8	2002/0043660	04/18/2002	Yamazaki <i>et al.</i> ✓				
	A9	2002/0084000	07/04/2002	Fitzgerald ✓				
	A10	2002/0096717	07/25/2002	Chu <i>et al.</i> ✓				
	A11	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i> ✓				
	A12	2002/0123167	09/05/2002	Fitzgerald ✓				
	A13	2002/0123183	09/05/2002	Fitzgerald ✓				
	A14	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i> ✓				
	A15	2002/0168864	11/14/2002	Cheng <i>et al.</i> ✓				
*	A16	2002/0185686	12/12/2002	Christiansen <i>et al.</i>				
<i>dm</i>	A17	2003/0003679	01/02/2003	Doyle <i>et al.</i> ✓		7		
	A18	2003/0013323	01/16/2003	Hammond <i>et al.</i> ✓				
	A19	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i> ✓				
	A20	2003/0041798	03/06/2003	Wenski <i>et al.</i> ✓				
	A21	2003/0057439	03/27/2003	Fitzgerald ✓				
	A22	2003/0102498	06/05/2003	Braithwaite <i>et al.</i> ✓				
	A23	2003/0199126	10/23/2003	Chu <i>et al.</i> ✓				
	A24	2003/0203600	10/30/2003	Chu <i>et al.</i> ✓				
	A25	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i> ✓				
	A26	2003/0218189	11/27/2003	Christiansen ✓				
	A27	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i> ✓				
	A28	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i> ✓				
	A29	2004/0014304	01/22/2004	Bhattacharyya ✓				
	A30	2004/0031979	02/19/2004	Lochtefeld ✓			06/06/2003	
	A31	2004/0041210	03/04/2004	Mouli ✓			09/02/2003	
EXAMINER <i>L. Melrose</i>				DATE CONSIDERED 10/19/2005				

* - Already listed on IDS (1449) filed on Nov. 5, 2004

FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-066			
INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Westhoff <i>et al.</i>			
				SERIAL NO.: 10/765,372			
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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>dm</i>	A32	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i> ✓			07/23/2003
	A33	4,010,045	03/01/1977	Ruchrwein ✓			
	A34	4,710,788	12/01/1987	Dambkes <i>et al.</i> ✓			
	A35	4,900,372	02/13/1990	Lee <i>et al.</i> ✓			
	A36	4,987,462	01/22/1991	Kim <i>et al.</i> ✓			
	A37	4,990,979	02/05/1991	Otto ✓			
	A38	4,997,776	03/05/1991	Harame <i>et al.</i> ✓			
	A39	5,013,681	05/07/1991	Godbey <i>et al.</i> ✓			
	A40	5,091,767	02/25/1992	Bean <i>et al.</i> ✓			
	A41	5,097,630	03/24/1992	Maeda <i>et al.</i> ✓			
	A42	5,155,571	10/13/1992	Wang <i>et al.</i> ✓			
	A43	5,159,413	10/27/1992	Calviello <i>et al.</i> ✓			
	A44	5,166,084	11/24/1992	Pfiester ✓			
	A45	5,177,583	01/05/1993	Endo <i>et al.</i> ✓			
	A46	5,202,284	04/13/1993	Kamins <i>et al.</i> ✓			
	A47	5,207,864	05/04/1993	Bhat <i>et al.</i> ✓			
	A48	5,208,182	05/04/1993	Narayan <i>et al.</i> ✓			
	A49	5,210,052	05/11/1993	Takasaki ✓			
	A50	5,212,110	05/18/1993	Pfiester <i>et al.</i> ✓			
	A51	5,221,413	06/22/1993	Brasen <i>et al.</i> ✓			
	A52	5,240,876	08/31/1993	Gaul <i>et al.</i> ✓			
	A53	5,241,197	08/31/1993	Murakami <i>et al.</i> ✓			
	A54	5,250,445	10/05/1993	Bean <i>et al.</i> ✓			
	A55	5,252,173	10/12/1993	Inoue ✓			
	A56	5,279,687	01/18/1994	Tuppen <i>et al.</i> ✓			
	A57	5,285,086	02/08/1994	Fitzgerald ✓			
↓	A58	5,291,439	03/01/1994	Kauffmann <i>et al.</i> ✓			
EXAMINER <i>A. H. Malin</i>				DATE CONSIDERED <i>10/19/05</i>			

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INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Westhoff <i>et al.</i>			
				SERIAL NO.: 10/765,372			
				FILING DATE: January 27, 2004 GROUP: 2842 2823			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>AM</i>	A59	5,298,452	03/29/1994	Meyerson ✓			
	A60	5,308,444	05/03/1994	Fitz <i>et al.</i> ✓			
	A61	5,310,451	05/10/1994	Tejwani <i>et al.</i> ✓			
	A62	5,316,958	05/31/1994	Meyerson ✓			
	A63	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i> ✓			
	A64	5,374,564	12/20/1994	Bruel ✓			
	A65	5,399,522	03/21/1995	Ohori ✓			
	A66	5,413,679	05/09/1995	Godbey ✓			
	A67	5,424,243	06/13/1995	Takasaki ✓			
	A68	5,425,846	06/20/1995	Koze <i>et al.</i> ✓			
	A69	5,426,069	06/20/1995	Selvakumar <i>et al.</i> ✓			
	A70	5,426,316	06/20/1995	Mohammad ✓			
	A71	5,442,205	08/15/1995	Brasen <i>et al.</i> ✓			
	A72	5,461,243	10/24/1995	Ek <i>et al.</i> ✓			
	A73	5,461,250	10/24/1995	Burghartz <i>et al.</i> ✓			
	A74	5,462,883	10/31/1995	Dennard <i>et al.</i> ✓			
	A75	5,476,813	12/19/1995	Naruse ✓			
	A76	5,479,033	12/26/1995	Baca <i>et al.</i> ✓			
	A77	5,484,664	01/16/1996	Kitahara <i>et al.</i> ✓			
	A78	5,523,243	06/04/1996	Mohammad ✓			
	A79	5,523,592	06/04/1996	Nakagawa <i>et al.</i> ✓			
	A80	5,534,713	07/09/1996	Ismail <i>et al.</i> ✓			
	A81	5,536,361	07/16/1996	Kondo <i>et al.</i> ✓			
	A82	5,540,785	07/30/1996	Dennard <i>et al.</i> ✓			
	A83	5,572,043	11/05/1996	Shimizu <i>et al.</i> ✓			
	A84	5,596,527	01/21/1997	Tomioka <i>et al.</i> ✓			
✓	A85	5,617,351	04/01/1997	Bertin <i>et al.</i> ✓			
EXAMINER <i>A. Melson</i>				DATE CONSIDERED 10/19/05			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>Exam</i> 	A86	5,630,905	05/20/1997	Lynch et al. ✓			
	A87	5,633,516	05/27/1997	Mishima ✓			
	A88	5,659,187	08/01/1997	Legoues et al. ✓			
	A89	5,683,934	11/04/1997	Candelaria ✓			
	A90	5,698,869	12/16/1997	Yoshimi et al. ✓			
	A91	5,714,777	02/03/1998	Ismail et al. ✓			
	A92	5,728,623	03/17/1998	Mori ✓			
	A93	5,739,567	04/14/1998	Wong ✓			
	A94	5,759,898	06/02/1998	Ek et al. ✓			
	A95	5,777,347	07/07/1998	Bartelink ✓			
	A96	5,786,612	07/28/1998	Otani et al. ✓			
	A97	5,786,614	07/28/1998	Chuang et al. ✓			
	A98	5,792,679	08/11/1998	Nakato ✓			
	A99	5,801,085	09/01/1998	Kim et al. ✓			
	A100	5,808,344	09/15/1998	Ismail et al. ✓			
	A101	5,810,924	09/22/1998	Legoues et al. ✓			
	A102	5,828,114	10/27/1998	Kim et al. ✓			
	A103	5,847,419	12/08/1998	Imai et al. ✓			
	A104	5,859,864	01/12/1999	Jewell ✓			
	A105	5,877,070	03/02/1999	Goesele et al. ✓			
	A106	5,891,769	04/06/1999	Liaw et al. ✓			
	A107	5,906,708	05/25/1999	Robinson et al. ✓			
	A108	5,906,951	05/25/1999	Chu et al. ✓			
	A109	5,912,479	06/15/1999	Mori et al. ✓			
	A110	5,943,560	08/24/1999	Chang et al. ✓			
	A111	5,963,817	10/05/1999	Chu et al. ✓			
	A112	5,966,622	10/12/1999	Levine et al. ✓			
	A113	5,998,807	12/07/1999	Lustig et al. ✓			
EXAMINER <i>ABMalsan</i>				DATE CONSIDERED <i>10/19/05</i>			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>Shm</i>	A114	6,010,937	01/04/2000	Karam et al. ✓			
	A115	6,013,134	01/11/2000	Chu et al. ✓			
	A116	6,030,884	02/29/2000	Mori ✓			
	A117	6,033,974	03/07/2000	Henley et al. ✓			
	A118	6,033,995	03/07/2000	Muller ✓			
	A119	6,039,803	03/21/2000	Fitzgerald et al. ✓			
	A120	6,058,044	05/02/2000	Sugiura et al. ✓			
	A121	6,059,895	05/09/2000	Chu et al. ✓			
	A122	6,074,919	06/13/2000	Gardner et al. ✓			
	A123	6,096,590	08/01/2000	Chan et al. ✓			
	A124	6,103,559	08/15/2000	Gardner et al. ✓			
	A125	6,107,653	08/22/2000	Fitzgerald ✓			
	A126	6,111,267	08/29/2000	Fischer et al. ✓			
	A127	6,117,750	09/12/2000	Bensahel et al. ✓			
	A128	6,124,617	09/26/2000	Ryum et al. ✓			
	A129	6,130,453	10/10/2000	Mei et al. ✓			
	A130	6,133,799	10/17/2000	Favors et al. ✓			
	A131	6,140,687	10/31/2000	Shimomura et al. ✓			
	A132	6,143,636	11/07/2000	Forbes et al. ✓			
	A133	6,153,495	11/28/2000	Kub et al. ✓			
	A134	6,154,475	11/28/2000	Soref et al. ✓			
	A135	6,160,303	12/12/2000	Fattaruso ✓			
	A136	6,162,688	12/19/2000	Gardner et al. ✓			
	A137	6,184,111	02/06/2001	Henley et al. ✓			
	A138	6,191,006	02/20/2001	Mori ✓			
	A139	6,191,007	02/20/2001	Matsui et al. ✓			
	A140	6,191,432	02/20/2001	Sugiyama et al. ✓			
✓	A141	6,194,722	02/27/2001	Fiorini et al. ✓			
EXAMINER <i>Shm</i>				DATE CONSIDERED <i>10/19/05</i>			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Am</i>	A142	6,204,529	03/20/2001	Lung <i>et al.</i> ✓			
	A143	6,207,977	03/27/2001	Augusto ✓			
	A144	6,210,988	04/03/2001	Howe <i>et al.</i> ✓			
	A145	6,218,677	04/17/2001	Broekaert ✓			
	A146	6,232,138	05/15/2001	Fitzgerald <i>et al.</i> ✓			
	A147	6,235,567	05/22/2001	Huang ✓			
	A148	6,242,324	06/05/2001	Kub <i>et al.</i> ✓			
	A149	6,249,022	06/19/2001	Lin <i>et al.</i> ✓			
	A150	6,251,755	06/26/2001	Furukawa <i>et al.</i> ✓			
	A151	6,261,929	07/17/2001	Gehrke <i>et al.</i> ✓			
	A152	6,266,278	07/24/2001	Harari <i>et al.</i> ✓			
	A153	6,271,551	08/07/2001	Schmitz <i>et al.</i> ✓			
	A154	6,271,726	08/07/2001	Fransis <i>et al.</i> ✓			
	A155	6,291,321	09/18/2001	Fitzgerald ✓			
	A156	6,313,016	11/06/2001	Kibbel <i>et al.</i> ✓			
	A157	6,316,301	11/13/2001	Kant ✓			
	A158	6,323,108	11/27/2001	Kub <i>et al.</i> ✓			
	A159	6,329,063	12/11/2001	Lo <i>et al.</i> ✓			
	A160	6,335,546	01/01/2002	Tsuda <i>et al.</i> ✓			
	A161	6,339,232	01/15/2002	Takagi ✓			
	A162	6,350,993	02/26/2002	Chu <i>et al.</i> ✓			
	A163	6,352,909	03/05/2002	Usenko ✓			
	A164	6,368,733	04/09/2002	Nishinaga ✓			
	A165	6,372,356	04/16/2002	Thornton <i>et al.</i> ✓			
	A166	6,399,970	06/04/2002	Kubo <i>et al.</i> ✓			
	A167	6,403,975	06/11/2002	Brunner <i>et al.</i> ✓			
	A168	6,406,589	06/18/2002	Yanagisawa ✓			
↓	A169	6,407,406	06/18/2002	Tezuka ✓			
EXAMINER <i>Amela</i>				DATE CONSIDERED 10/19/05			

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INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Westhoff <i>et al.</i>			
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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Abm</i>	A170	6,420,937	07/16/2002	Akatsuka <i>et al.</i> ✓			
	A171	6,425,951	07/30/2002	Chu <i>et al.</i> ✓			
	A172	6,429,061	08/06/2002	Rim ✓			
	A173	6,482,749	11/19/2002	Billington <i>et al.</i> ✓			
	A174	6,518,644	02/11/2003	Fitzgerald ✓			
	A175	6,521,041	02/18/2003	Wu <i>et al.</i> ✓			
	A176	6,524,935	02/25/2003	Canaperi <i>et al.</i> ✓			
	A177	6,525,338	02/25/2003	Mizushima <i>et al.</i> ✓			
	A178	6,555,839	04/29/2003	Fitzgerald ✓			
	A179	6,573,126	06/03/2003	Cheng <i>et al.</i> ✓			
	A180	6,576,532	06/10/2003	Jones <i>et al.</i> ✓			
	A181	6,583,015	06/24/2003	Fitzgerald <i>et al.</i> ✓			
	A182	6,593,191	07/15/2003	Fitzgerald ✓			
	A183	6,594,293	07/15/2003	Bulsara <i>et al.</i> ✓			
	A184	6,602,613	08/05/2003	Fitzgerald ✓			
	A185	6,603,156	08/05/2003	Rim ✓			
	A186	6,646,322	11/11/2003	Fitzgerald ✓			
	A187	6,649,480	11/18/2003	Fitzgerald <i>et al.</i> ✓			
	A188	6,677,192	01/13/2004	Fitzgerald ✓			
	A189	6,703,144	03/09/2004	Fitzgerald ✓			03/18/2003
	A190	6,703,688	03/09/2004	Fitzgerald ✓			07/16/2001
	A191	6,709,903	03/23/2004	Christiansen ✓			04/30/2003
	A192	6,713,326	03/30/2004	Cheng <i>et al.</i> ✓			03/04/2003
	A193	6,723,661	04/20/2004	Fitzgerald ✓			07/16/2001
	A194	6,724,008	04/20/2004	Fitzgerald ✓			07/16/2001
	A195	6,730,551	05/04/2004	Lee <i>et al.</i> ✓			08/02/2002
	A196	6,737,670	05/18/2004	Cheng <i>et al.</i> ✓			03/07/2003
	A197	6,750,130	06/15/2004	Fitzgerald ✓			01/07/2001
EXAMINER <i>Abm</i>				DATE CONSIDERED <i>10/19/05</i>			

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U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Alm</i>	B1	41 01 167	07/23/1992	DE ✓	/			N	Y (Abstract only)
	B2	0 514 018	11/19/1992	EP ✓				N	Y
	B3	0 587 520	03/16/1994	EP ✓				N	Y
	B4	0 683 522	11/22/1995	EP ✓				N	Y
	B5	0 828 296	03/11/1998	EP ✓				N	Y
	B6	0 829 908	03/18/1998	EP ✓				N	Y
	B7	0 838 858	04/29/1998	EP ✓				N	Y (Abstract only)
	B8	1 020 900	07/19/2000	EP ✓				N	Y
	B9	1 174 928	01/23/2002	EP ✓				N	Y
	B10	2 342 777	04/19/2000	GB ✓				Y	Y
	B11	2-210816	08/22/1990	JP ✓				N	Y (Abstract only)
	B12	3-36717	02/18/1991	JP ✓				N	N
	B13	4-307974	10/30/1992	JP ✓				N	N
	B14	5-166724	07/02/1993	JP ✓				N	Y (Abstract only)
	B15	6-177046	06/24/1994	JP ✓				N	Y (Abstract only)
	B16	6-244112	09/02/1994	JP ✓				Y	Y
	B17	6-252046	09/09/1994	JP ✓				Y	Y
	B18	7-94420	04/07/1995	JP ✓				N	Y (Abstract only)
	B19	7-106446	04/21/1995	JP ✓				N	N
	B20	7-240372	09/12/1995	JP ✓				N	Y (Abstract only)
	B21	10-270685	10/09/1998	JP ✓				N	Y
↓	B22	11-233744	08/27/1999	JP ✓				N	N
EXAMINER <i>Alm</i>					DATE CONSIDERED <i>10/19/05</i>				

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INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-066

APPLICANT(S): Westhoff *et al.*

SERIAL NO.: 10/765,372

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U.S. PATENT DOCUMENTS

EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

EXAM INIT.	DOCUMENT NUMBER	DATE	COUN- TRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>pm</i>	B23	61-141116	06/28/1986	JP	/		N	Y (Abstract only)
	B24	2000-021783	01/21/2000	JP	/		N	Y
	B25	2000-031491	01/28/2000	JP	/		N	Y
	B26	2000-513507	10/10/2000	JP	/		Y	N
	B27	2001-319935	11/16/2001	JP	/		N	Y
	B28	2002-076334	03/15/2002	JP	/		N	Y
	B29	2002-164520	06/07/2002	JP	/		N	Y
	B30	2002-289533	10/04/2002	JP	/		N	Y
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EXAMINER

A. H. Malson

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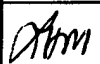


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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff <i>et al.</i> SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: 2812 ²⁸²³					
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	B50	04/006311 ✓	01/15/2004	WO				N	Y
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
Arm	C2	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest (1995 International Electron Devices Meeting)</u> , pp. 761-764.							
	C3	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.							
	C4	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.							
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	C6	Borenstein <i>et al.</i> , "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999), pp. 205-210.							
↓	C7	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS experimental study," <u>IEEE</u> (1996), pp. 21.2.1-21.2.4.							
EXAMINER <u>Arm</u>					DATE CONSIDERED <u>10/19/05</u>				

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	C8 C9 C10 C11 C12 C13 C14 C15 C16 C17 C18 C19	<p>Bruel <i>et al.</i>, "©SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179.</p> <p>Bruel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u>, Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202.</p> <p>Bufler <i>et al.</i>, "Hole transport in strained Si_{1-x}Ge_x alloys on Si_{1-x}Ge_x substrates," <u>Journal of Applied Physics</u>, Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602.</p> <p>Bulsara, "Materials Issues with the Integration of Lattice-Mismatched In_xGa_{1-x}As on GaAs," PhD Thesis, MIT, June 1998, pp. 1-178.</p> <p>Bulsara <i>et al.</i>, "Relaxed In_xGa_{1-x}As graded buffers grown with organometallic vapor phase epitaxy on GaAs," <u>Applied Physics Letters</u>, Vol. 72, No. 13 (March 30, 1998), pp. 1608-1610.</p> <p>Burghartz <i>et al.</i>, "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u>, Vol. 44, No. 1 (January 1996), pp. 100-104.</p> <p>Buttard <i>et al.</i>, "Toward Two-Dimensional Self-Organization of Nanostructures Using Wafer Bonding and Nanopatterned Silicon Surfaces," <u>IEEE - 2002 Journal of Quantum Electronics</u>, Vol. 38, Issue 8 (August 2002), pp. 995-1005.</p> <p>Canaperi <i>et al.</i>, "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002), abstract.</p> <p>Carlin <i>et al.</i>, "High Efficiency GaAs-on-Si Solar Cells with High Voc using Graded GeSi Buffers," <u>IEEE - 2000</u> (2000), pp. 1006-1011.</p> <p>Carlin <i>et al.</i>, "Investigation and Development of High Quality GaAs-on-Si for Space Photovoltaics Using a Graded GeSi," PhD Thesis, Ohio State University, 2001, pp. 1-232.</p> <p>Chang <i>et al.</i>, "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u>, No. 1 (January 1991), pp. 202-204.</p> <p>Charasse <i>et al.</i>, "MBE Growth of GaAs on Si at Thomson," <u>IEE Colloquium on GaAs on Si</u>, (8 Mar 1988), pp. 1-4</p>								
EXAMINER				DATE CONSIDERED 10/19/05						

FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-066					
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
Am	C20	Cheng <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323.							
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	C23	Cullis <i>et al.</i> , "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994), pp. 1924-1931.							
	C24	Currie <i>et al.</i> , "Carrier mobilities and process stability of strained Si n- and p-MOSFETs on SiGe virtual substrates," <u>Journal of Vacuum Science and Technology B</u> , Vol. 19, No. 6 (Nov/Dec 2001), pp. 2268-2279.							
	C25	Currie <i>et al.</i> , "Controlling Threading Dislocation Densities in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," <u>Applied Physics Letters</u> , Vol. 72, Issue 14 (04/06/98), pp. 1718-1720.							
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	C30	Feichtinger <i>et al.</i> , "Misfit Dislocation Nucleation Study in p/p+ Silicon," <u>Journal of the Electrochemical Society</u> , 148 (7) (2001), pp. G379-G382.							
	C31	Feijoo <i>et al.</i> , "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pp. 493-496.							
↓	C32	Fischetti <i>et al.</i> , "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>Journal of Applied Physics</u> , Vol. 80, No. 4 (August 15, 1996), pp. 2234-2252.							
EXAMINER <i>A. H. Malsam</i>				DATE CONSIDERED <i>10/19/2005</i>					

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<i>Am</i>	C33	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electronmobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001), pp. 1232-1250.							
	C34	Fitzgerald, "Dislocations in strained-layer epitaxy: theory, experiment, and applications," <u>Materials Science Reports</u> , Vol. 7 (1991), pp. 87-142.							
	C35	Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61.							
	C36	Fitzgerald <i>et al.</i> , "GeSi/Si Nanostructures," <u>Department of Materials Science, M.I.T.</u> , (1995), pp. 1-15.							
	C37	Fitzgerald <i>et al.</i> , "Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>American Vacuum Society</u> , (1992) pp. 1807-1819.							
	C38	Fitzgerald <i>et al.</i> , "Totally Relaxed Ge _x Si _{1-x} Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pp. 811-813.							
	C39	Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277.							
	C40	Giovane <i>et al.</i> , "Strain-Balanced Silicon-Germanium Materials for Near IR Photodetection in Silicon-Based Optical Interconnects," PhD Thesis, MIT, 1998, pp. 1-134.							
	C41	Godbey <i>et al.</i> , "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si _{0.7} Ge _{0.3} Layer as an Etch Stop," <u>Journal of the Electrical Society</u> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.							
	C42	Gray <i>et al.</i> , "Analysis and Design of Analog Integrated Circuits," John Wiley & Sons, 1984, pp. 605-632.							
	C43	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al _x Ga _{1-x}) _{0.5} In _{0.5} P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (April 15, 2002), pp. 4891-4899.							
	C44	Groenert <i>et al.</i> , "Strategies for Direct Monolithic Integration of Al _x Ga _(1-x) As/In _x Ga _(1-x) As LEDS and Lasers on Ge/GeSi/Si Substrates Via Relaxed Graded Ge _x Si _(1-x) Buffer Layers," <u>Materials Research Society Symposium Proceedings</u> , Vol. 692 (2002), pp. H.9.30.1-H.9.30.6.							
	C45	Grützmacher <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533.							
	C46	Hackbarth <i>et al.</i> , "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151.							
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
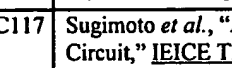
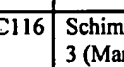
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
<div style="text-align: center;">  </div>	C47	Hackbarth <i>et al.</i> , "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999), pp. 734-738.							
	C48	Halsall <i>et al.</i> , "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaInP system," <u>Journal of Applied Physics</u> , Vol. 85, No. 1 (Jan. 1999), pp. 199-202							
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	C53	Houghton, "Strain Relaxation Kinetics in Si _{1-x} Ge _x /Si Heterostructures," <u>Journal of Applied Physics</u> , Vol. 70, No. 4 (August 15, 1991), pp. 2136-2151.							
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<div style="text-align: center;">  </div>	C59	Ishikawa <i>et al.</i> , "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings of the 1997 IEEE International SOI Conference</u> (October 1997), pp. 16-17.							
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	C60	Ishikawa <i>et al.</i> , "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985.							
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	C62	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," Electron Devices Meeting, Washington, D.C. (December 10, 1995), pp. 20.1.1-20.1.4.							
	C63	Kearney <i>et al.</i> , "The effect of alloy scattering on the mobility of holes in a Si _{1-x} Ge _x quantum well," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 174-180.							
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	C65	Kissinger, <i>et al.</i> "Stepwise Equilibrated Graded Ge ₂ Si _{1-x} Buffer With Very Low Threading Dislocation Density on Si(001)," <u>Applied Physics Letters</u> Vol. 66, No. 16 (Apr. 17, 1995), pp. 2083-2085.							
	C66	Knall <i>et al.</i> , "The Use of Graded in GaAs Layers and Patterned Substrates to Remove Threading Dislocations From GaAs on Si," <u>Journal of Applied Physics</u> , Vol. 76, Issue 5 (September 1, 1994), pp. 2697-2702.							
	C67	Koester <i>et al.</i> , "Extremely High Transconductance Ge/Si _{0.4} Ge _{0.6} p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000), pp. 110-112.							
	C68	König <i>et al.</i> , "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.							
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	C70	König <i>et al.</i> , "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995), pp. 1595-1602.							
	C71	Kummer <i>et al.</i> , "Low energy plasma enhanced chemical vapor deposition," <u>Materials Science and Engineering</u> , B89 (2002), pp. 288-295.							
↓	C72	Kuznetsov <i>et al.</i> , "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>Journal of Vacuum Science and Technology</u> , B 13(6) (November/December 1995), pp. 2892-2896.							
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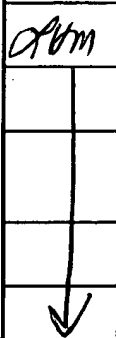

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<i>abm</i> <div style="border-left: 1px solid black; height: 100px; margin-left: 5px;"></div>	C73	Langdo, "High Quality Ge on Si by Epitaxial Necking," <u>Applied Physics Letters</u> , Vol. 76, Issue 25 (June 19, 2000), pp. 3700-3702.							
	C74	Langdo et al., (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" <u>IEEE International SOI Conference</u> , pages 211-212 (XP002263057)							
	C75	Larson, "Integrated Circuit Technology Options for RFIC's Present Status and Future Directions," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3 (March 1998), pp. 387-399.							
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INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Westhoff <i>et al.</i>					
				SERIAL NO.: 10/765,372					
				FILING DATE: January 27, 2004 GROUP: 2812 ²⁸²³					
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	C133	Xie <i>et al.</i> , "Very High Mobility Two-Dimensional Hole Gas in Si/Ge _x Si _{1-x} /Ge Structures Grown by Molecular Beam Epitaxy," <u>Applied Physics Letters</u> , Vol. 63, Issue 16 (October 18, 1993), pp. 2263-2264.							
<div style="border-left: 1px solid black; height: 100px; margin-left: 5px;"></div>	C134	Xie, "SiGe Field Effect Transistors," <u>Materials Science and Engineering</u> , Vol. 25 (1999), pp. 89-121.							
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SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENTAPR 18 2005
PATENT & TRADEMARK OFFICE

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* - Already listed on the IDS (1449) filed on Nov. 5, 2004